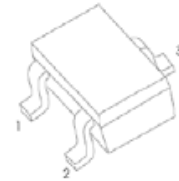


SOT-523 Plastic-Encapsulate Transistors

FEATURES

- Low Cob: Cob=2.0pF(Typ)
- Complement to 2SA1774



1. BASE 2. EMITTER 3. COLLECTOR

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current -Continuous	150	mA
P _C	Collector Power Dissipation	150	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

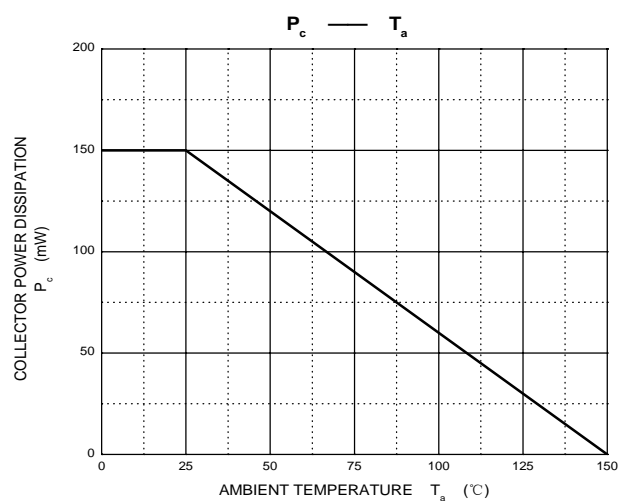
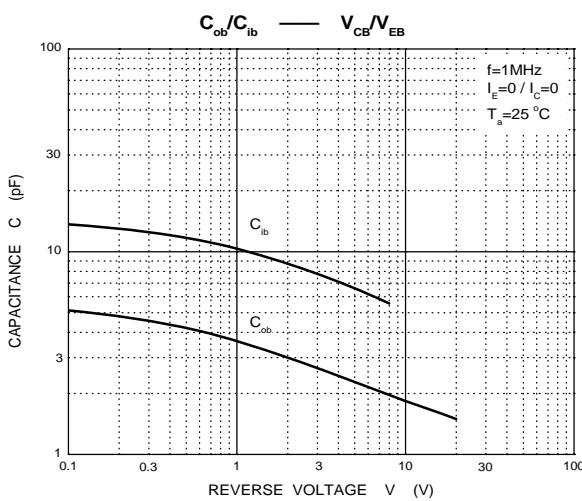
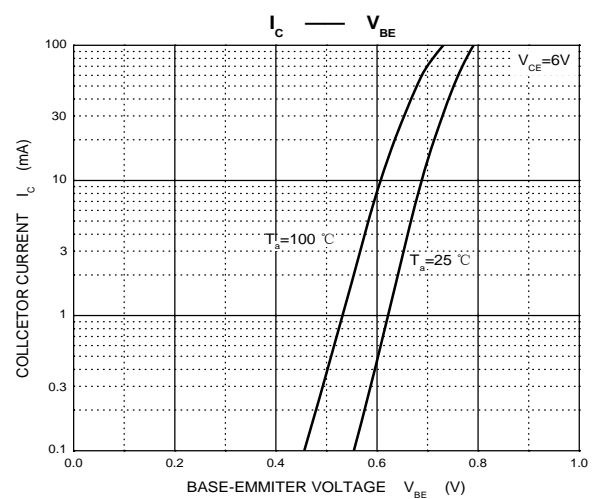
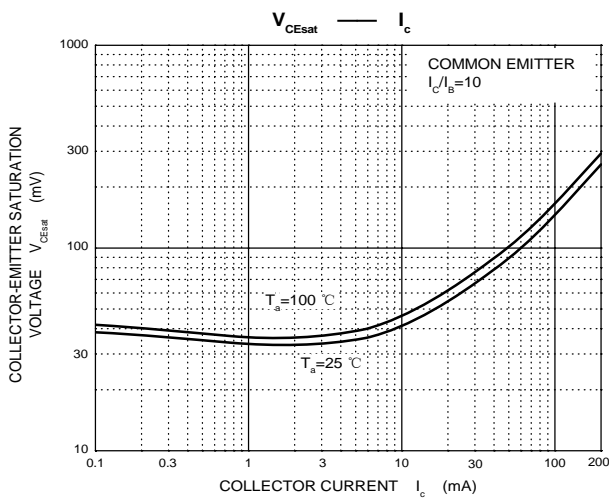
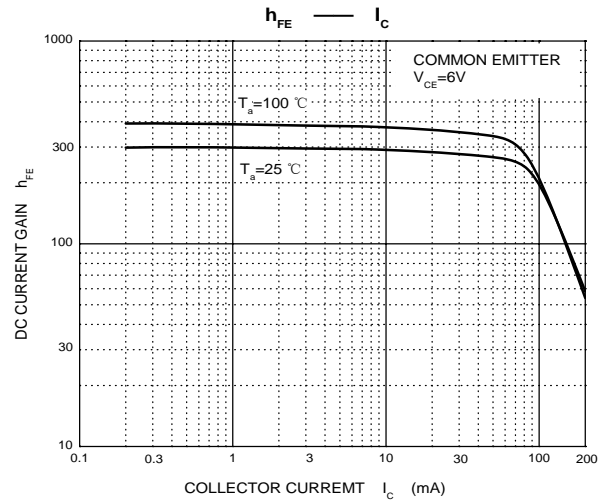
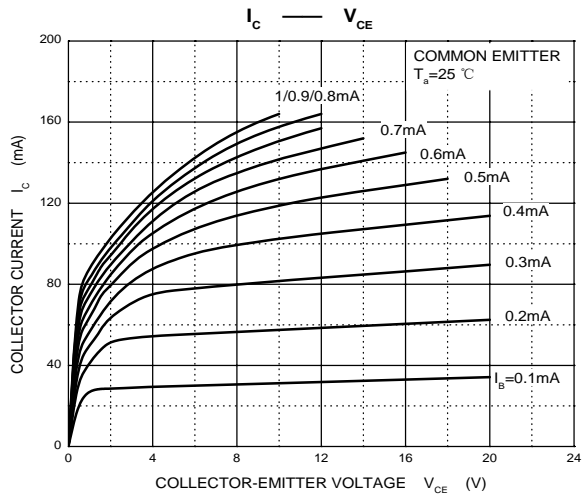
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =50μA, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =50μA, I _C =0	7			V
Collector cut-off current	I _{CBO}	V _{CB} =60V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =7V, I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =6V, I _C =1mA	120		560	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =50mA, I _B =5mA			0.4	V
Transition frequency	f _T	V _{CE} =12V, I _C =2mA, f=100MHz		180		MHz
Collector output capacitance	C _{ob}	V _{CB} =12V, I _E =0, f=1MHz			3.5	pF

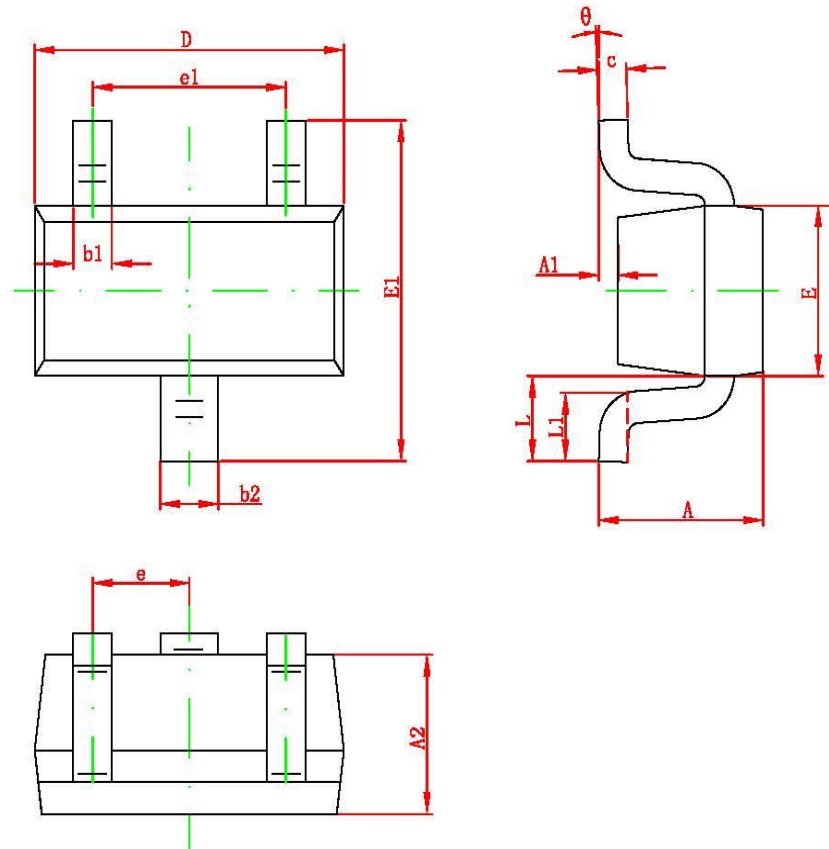
CLASSIFICATION OF h_{FE}

Rank	Q	R	S
Range	120-270	180-390	270-560
Marking	BQ	BR	BS

Typical Characteristics



SOT-523 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°